# imall

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We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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### **N-Channel Power MOSFET**

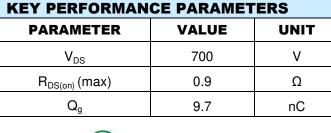
700V, 4.5A, 0.9Ω

#### **FEATURES**

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

#### **APPLICATION**

- Power Supply
- Lighting

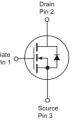












Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (DPAK) per J-STD-020.

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>c</sub> = 25°C unless otherwise noted)							
PARAMETER		SYMBOL	IPAK/DPAK	ITO-220	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	7	V			
Gate-Source Voltage		$V_{GS}$	±	V			
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$		4	A			
	T <sub>C</sub> = 100°C		2				
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	1	А			
Total Power Dissipation @ $T_C = 25^{\circ}C$		P <sub>DTOT</sub>	50 20		W		
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	64		mJ		
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	1.6		А		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 t	°C			

THERMAL PERFORMANCE						
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT		
Junction to Case Thermal Resistance	R <sub>eJC</sub>	2.5	°C/W			
Junction to Ambient Thermal Resistance	R <sub>eja</sub>	6	°C/W			

Notes: R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R<sub>BJA</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design. ReJA shown below for single device operation on FR-4 PCB in still air.





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ELECTRICAL SPECIFICATIONS (T <sub>c</sub> = 25°C unless otherwise noted)							
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT	
Static (Note 4)							
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	700			V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	2.0	3.1	4.0	V	
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA	
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA	
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.5A$	R <sub>DS(on)</sub>		0.83	0.9	Ω	
Dynamic (Note 5)							
Total Gate Charge	$V_{DS} = 380V, I_{D} = 2.3A,$ $V_{GS} = 10V$	Qg		9.7		nC	
Gate-Source Charge		Q <sub>gs</sub>		2.9			
Gate-Drain Charge		Q <sub>gd</sub>		3.5			
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		482		pF	
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		34			
Gate Resistance	F = 1MHz, open drain	R <sub>g</sub>		3.6		Ω	
Switching (Note 6)							
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 40\Omega,$ $I_{D} = 2.3A, V_{GS} = 10V,$	t <sub>d(on)</sub>		20			
Turn-On Rise Time		t <sub>r</sub>		54		ns	
Turn-Off Delay Time		t <sub>d(off)</sub>		34			
Turn-Off Fall Time	$I_{\rm D} = 2.3 \text{A}, V_{\rm GS} = 10 \text{V},$	t <sub>f</sub>		48			
Source-Drain Diode (Note 4)				·	·		
Forward On Voltage	$I_{\rm S} = 4.5 {\rm A}, V_{\rm GS} = 0 {\rm V}$	V <sub>SD</sub>			1.4	V	
Reverse Recovery Time	V <sub>R</sub> =200V, I <sub>S</sub> = 2.3A dI <sub>F</sub> /dt = 100A/µs	t <sub>rr</sub>		176		ns	
Reverse Recovery Charge		Q <sub>rr</sub>		1.1		μC	

#### Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 50mH, I\_{AS} = 1.6A, V\_{DD} = 50V, R\_G = 25\Omega, Starting T\_J =  $25^{\circ}C$ 

4. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



#### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING			
TSM70N900CI C0G	ITO-220	50pcs / Tube			
TSM70N900CH C5G	TO-251 (IPAK)	75pcs / Tube			
TSM70N900CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel			

Note:

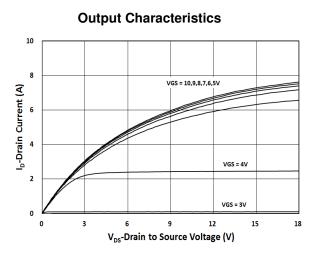
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

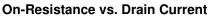
2. Halogen-free according to IEC 61249-2-21 definition

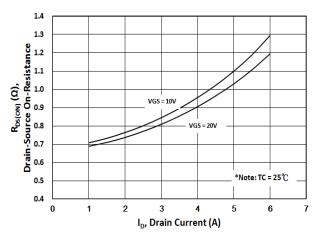


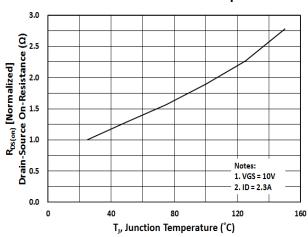
#### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 





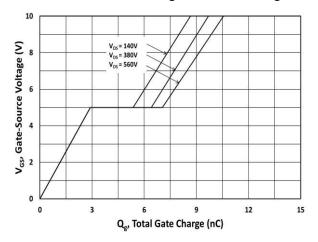


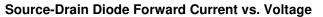


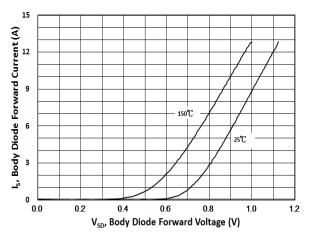
**On-Resistance vs. Junction Temperature** 

Transfer Characteristics

Gate-Source Voltage vs. Gate Charge



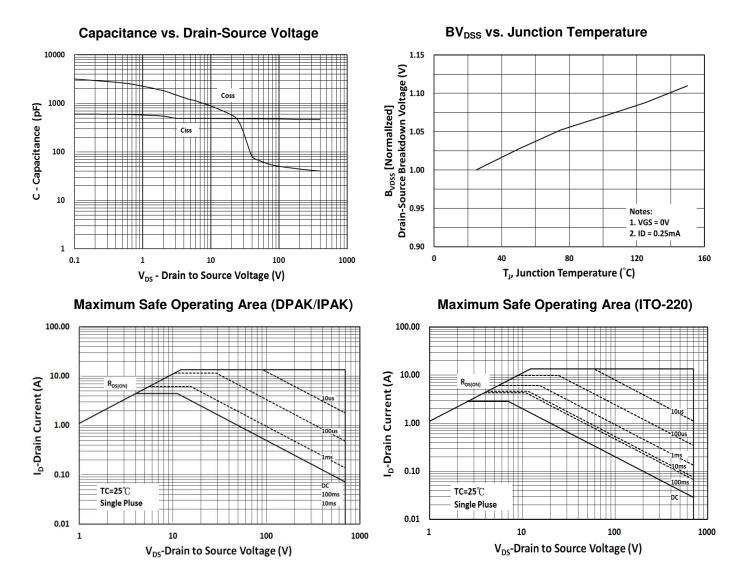






#### **CHARACTERISTICS CURVES**

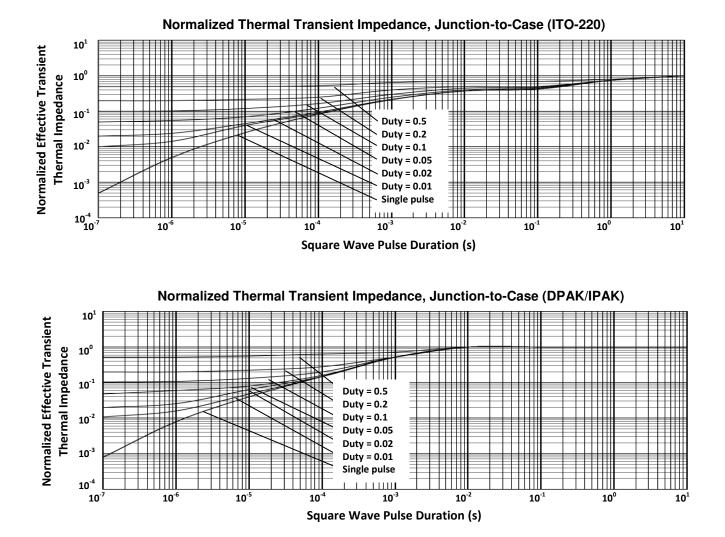
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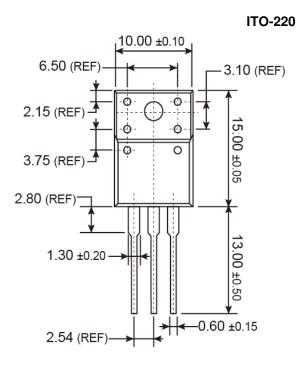
#### **ELECTRICAL CHARACTERISTICS CURVES**

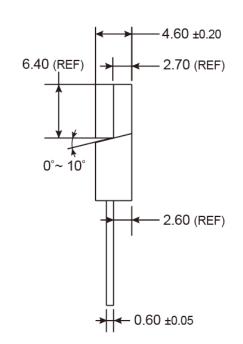
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$ 





#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





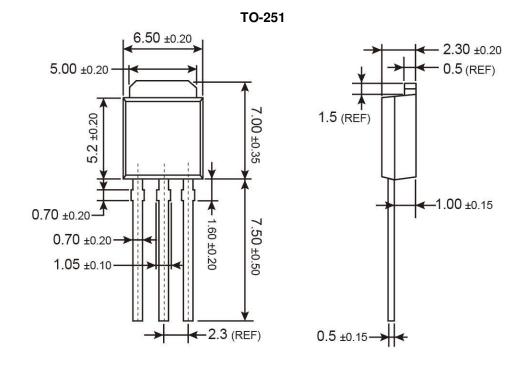
#### **MARKING DIAGRAM**



- G = Halogen Free
- **Y** = Year Code
- **WW** = Week Code (01 $\sim$ 52)
  - **F** = Factory Code



#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



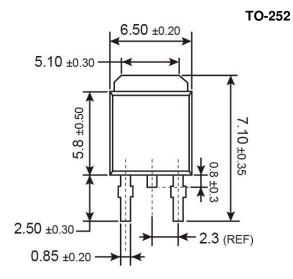
#### **MARKING DIAGRAM**

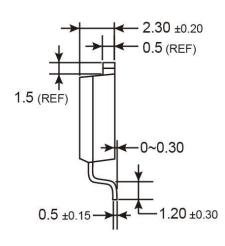
	Y	= Year Code						
5	Μ	= Month Code for Halogen Free Product						
70N900		<b>O</b> =Jan	Ρ	=Feb	Q	=Mar	R	=Apr
		<b>S</b> =May	Т	=Jun	U	=Jul	۷	=Aug
		W =Sep	Х	=Oct	Υ	=Nov	Ζ	=Dec
	L	= Lot Code (1	~9, /	A∼Z)				
#1								

Document Number: DS\_P0000140

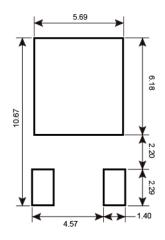


#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

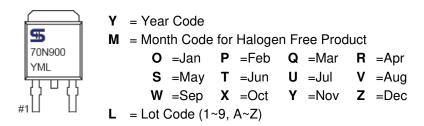




#### SUGGESTED PAD LAYOUT (Unit: Millimeters)



#### **MARKING DIAGRAM**





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